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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

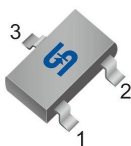
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



TSM210N02CX

20V N-Channel Power MOSFET

SOT-23



Pin Definition:

1. Gate
2. Source
3. Drain

Key Parameter Performance

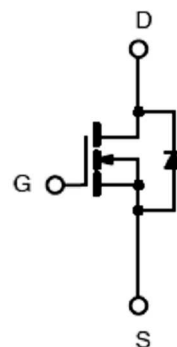
Parameter		Value	Unit
V_{DS}		20	V
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	21	m Ω
	$V_{GS} = 2.5V$	25	
	$V_{GS} = 1.8V$	32	
Q_g		5.8	nC

Ordering Information

Part No.	Package	Packing
TSM210N02CX RFG	SOT-23	3kpcs / 7_Reel

Note: 'G' denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 10	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	6.7	A
	$T_C = 100^\circ\text{C}$		4.2	A
Pulsed Drain Current ^(Note 1)		I_{DM}	26.8	A
Power Dissipation @ $T_C = 25^\circ\text{C}$		P_D	1.56	W
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	80	$^\circ\text{C/W}$

Electrical Specifications ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	20	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 4A$	$R_{DS(ON)}$	--	19	21	mΩ
	$V_{GS} = 2.5V, I_D = 3A$		--	22	25	
	$V_{GS} = 1.8V, I_D = 2A$		--	26	32	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	0.3	0.6	0.8	V
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
	$V_{DS} = 16V, T_J = 125^{\circ}C$		--	--	10	
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I_{GSS}	--	--	±100	nA
Forward Transconductance ^(Note 2)	$V_{DS} = 10V, I_S = 4A$	g_{fs}	--	9.5	--	S
Dynamic						
Total Gate Charge ^(Note 2,3)	$V_{DS} = 10V, I_D = 4A,$ $V_{GS} = 4.5V$	Q_g	--	5.8	--	nC
Gate-Source Charge ^(Note 2,3)		Q_{gs}	--	0.6	--	
Gate-Drain Charge ^(Note 2,3)		Q_{gd}	--	2	--	
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	600	--	pF
Output Capacitance		C_{oss}	--	70	--	
Reverse Transfer Capacitance		C_{rss}	--	45	--	
Switching						
Turn-On Delay Time ^(Note 2,3)	$V_{DD} = 10V, I_D = 1A,$ $V_{GS} = 4.5V, R_{GEN} = 25\Omega$	$t_{d(on)}$	--	5.0	--	ns
Turn-On Rise Time ^(Note 2,3)		t_r	--	14.4	--	
Turn-Off Delay Time ^(Note 2,3)		$t_{d(off)}$	--	30.0	--	
Turn-Off Fall Time ^(Note 2,3)		t_f	--	9.2	--	
Source-Drain Diode Ratings and Characteristic						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	6.7	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	26.8	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = 1A$	V_{SD}	--	--	1	V

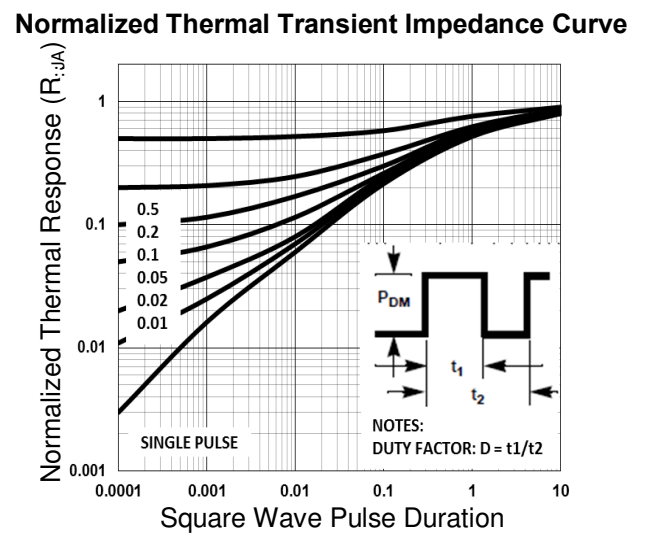
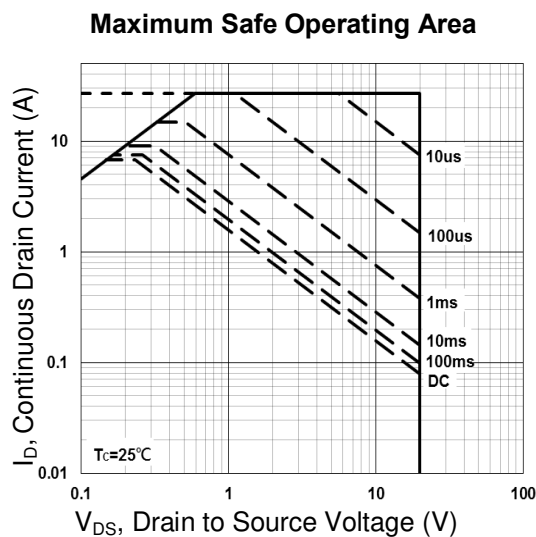
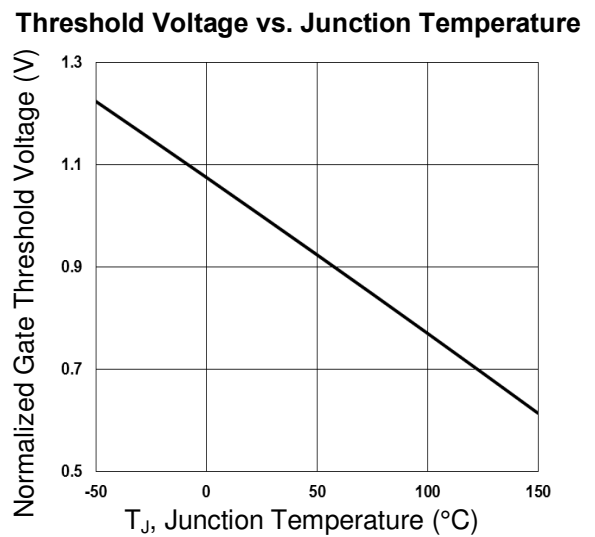
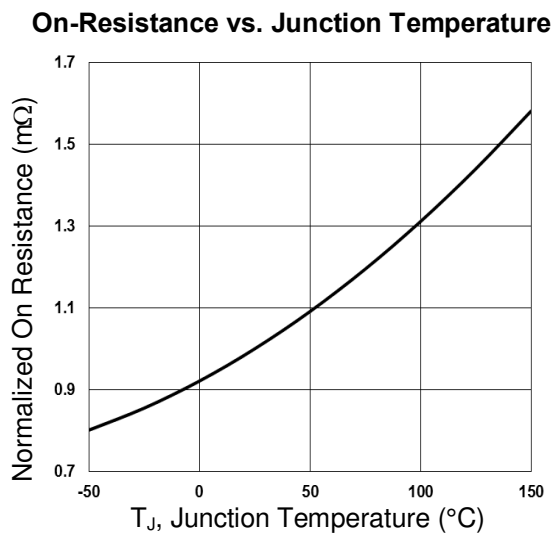
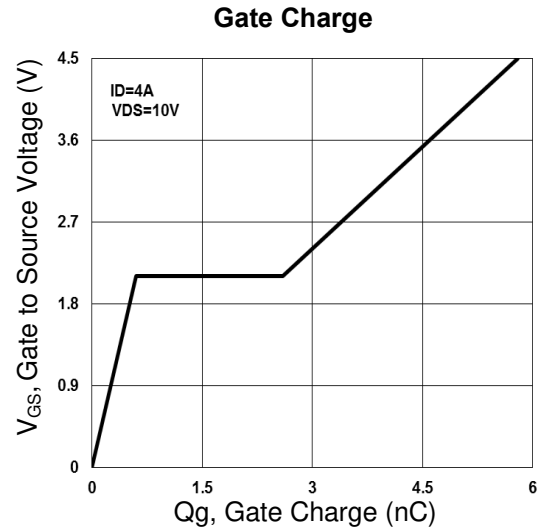
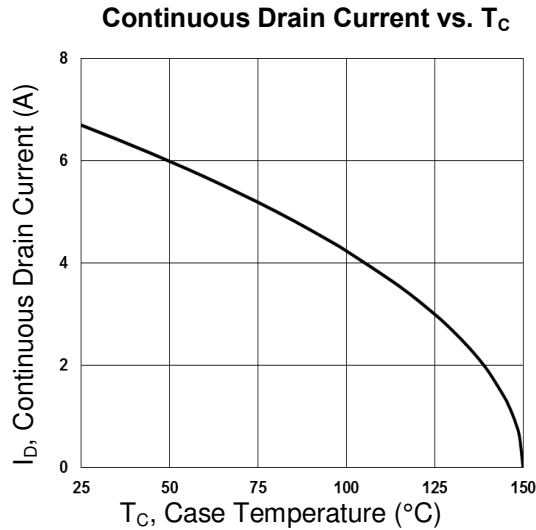
Note:

- Pulse width limited by safe operating area
- Pulse test: pulse width $\neq 300\mu s$, duty cycle $\neq 2\%$
- Switching time is essentially independent of operating temperature.

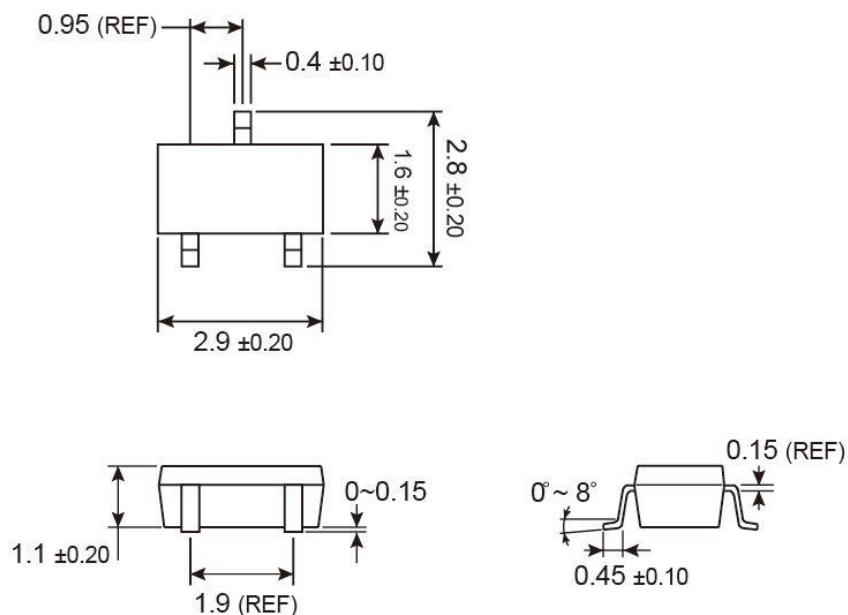
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20V N-Channel Power MOSFET

Electrical Characteristics Curve

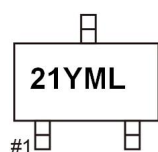


SOT-23 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- 21** = Device Code
- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

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